High resolution STEM of quantum dots and quantum wires

This article reviews the application of high resolution scanning transmission electron microscopy (STEM) to semiconductor quantum dots (QDs) and quantum wires (QWRs). Different imaging and analytical techniques in STEM are introduced and key examples of their application to QDs and QWRs are presented. In addition, the benefits offered by aberration correction are discussed and an outlook for future developments of high resolution STEM analysis of QDs and QWRs is given.

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